SGS-THOMSON MICROELECTRONICS

74LCX16374

LOW VOLTAGE 16-BIT D-TYPE FLIP FLOP 3-STATE WITH 5V TOLERANT INPUTS AND OUTPUTS

- 5V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED:
 f_{MAX} = 170 MHz (MIN.) at V_{CC} = 3V
- POWER-DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: IOH = IOL = 24 mA (MIN)
- PCI BUS LEVELS GUARANTEED AT 24mA
- BALANCED PROPAGATION DELAYS: $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2.0V to 3.6V (1.5V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 16374
- LATCH-UP PERFORMANCE EXCEEDS 500mA
- ESD PERFORMANCE: HBM >2000V; MM > 200V

DESCRIPTION

The LCX16374 is a low voltage CMOS 16-BIT D-TYPE FLIP FLOP with 3 STATE OUTPUT NON INVERTING fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology. It is ideal for low power and high speed applications; it can be interfaced to 5V signal enviroment for both inputs and outputs.

These 16 bit D-Type flip-flops are controlled by two clock inputs (nCK) and two output enable inputs (nOE).

On the positive transition of the (nCK), the nQ outputs will be set to the logic state that were setup at the <u>nD</u> inputs.

While the $(n\overline{OE})$ input is low, the 8 outputs (nQ) will be in a normal state (high or low logic level) and while high level the outputs will be in a high impedance state.

Any output control does not affect the internal operation of flip flops; that is, the old data can be retained or the new data can be entered even while the outputs are off.

It has better speed performance at 3.3V than 5V LSTTL family combined with the true CMOS low power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

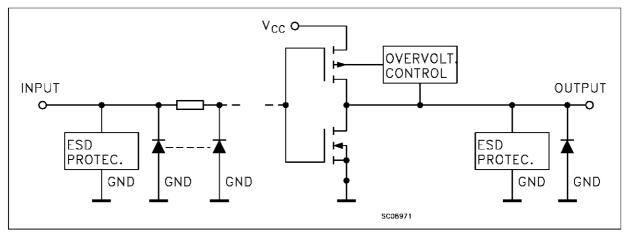




PIN CONNECTION

] 48	1CK
1 Q ₀ 2 [47	1 D _o
1Q ₁ з[45	1 D ₁
GND ₄[] 45	GND
1 Q ₂ 5] 44	1 D ₂
1 Q ₃ 6 [43	1 D 3
V _{cc} 7 [42	V _{CC}
1Q ₄ в[41	1 D ₄
1 Q ₅ 9 [40	1 D ₅
GND 10	39	GND
1 Q ₆ 11 [38	1 D ₆
1 Q7 12 [37	1 D ₇
2 Q _D 13 [36	2 D ₀
2Q ₁ 14 [35	2 D 1
GND 15	34	GND
2Q ₃ 15	33	2 D ₂
2Q3 17	32	2 D 3
V _{сс} 18 [31	V _{cc}
2Q4 19	30	2 D 4
2 Q ₅ 20 [29	2 D 5
GND 21	28	GND
2 Q ₆ 22 [27	2 D ₆
2 Q ₇ 23 [26	2 D 7
20E 24 [25	2CK
L	PC1201D	

INPUT AND OUTPUT EQUIVALENT CIRCUIT



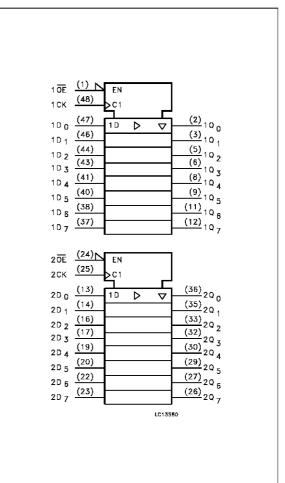
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	10E	3 State Output Enable Input (Active LOW)
2, 3, 5, 6, 8, 9, 11, 12	1Q0 to 1Q7	Data Inputs
13, 14, 16, 17, 19, 20, 22, 23	2Q0 to 2Q7	Data Inputs
24	20E	3 State Output Enable Input (Active LOW)
25	2CK	Clock Input (LOW to HIGH, edge triggered)
36, 35, 33, 32, 30, 29, 27, 26	2D0 to 2D7	3 State Outputs
47, 46, 44, 43, 41, 40, 38, 37	1D0 to 1D7	3 State Outputs
48	1CK	Clock Input (LOW to HIGH, edge triggered)
4, 10, 15, 21, 28, 34, 39, 45	GND	Ground (0V)
7, 18, 31, 42	Vcc	Positive Supply Voltage

TRUTH TABLE

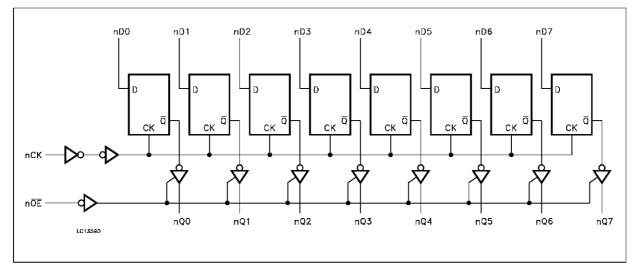
	INPUTS			
OE	СК	D	Q	
Н	Х	Х	Z	
L		Х	NO CHANGE	
L		L	L	
L		Н	Н	

IEC LOGIC SYMBOLS





LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to + 7.0	V
VI	DC Input Voltage	-0.5 to + 7.0	V
Vo	DC Output Voltage (OFF state)	-0.5 to + 7.0	V
Vo	DC Output Voltage (High or Low State) (note1)	-0.5 to V_{CC} + 0.5	V
Ιικ	DC Input Diode Current	- 50	mA
I _{OK}	DC Output Diode Current (note2)	± 50	mA
lo	DC Output Source/Sink Current	± 50	mA
I_{CC} or I_{GND}	DC V _{CC} or Ground Current Per Supply Pin	± 100	mA
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. 1) Io absolute maximum rating must be observed

2) Vo < GND, Vo > Vcc

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage (note 1)	2.0 to 3.6	V
VI	Input Voltage	0 to 5.5	V
Vo	Output Voltage (OFF state)	0 to 5.5	V
Vo	Output Voltage (High or Low State)	0 to V _{CC}	V
I _{OH} , I _{OL}	High or Low Level Output Current ($V_{CC} = 3.0$ to 3.6V)	± 24	mA
I _{OH} , I _{OL}	High or Low Level Output Current ($V_{CC} = 2.7$ to 3.0V)	± 12	mA
T _{op}	Operating Temperature:	-40 to +85	°C
dt/dv	Input Transition Rise or Fall Rate ($V_{CC} = 3.0V$) (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V 2) V_{IN} from 0.8V to 2.0V



DC SPECIFICATIONS

Symbol	Parameter	Tes	t Condit	ions	Val	ue	Unit
		Vcc	Vcc		-40 to 85 °C		
		(V)			Min.	Max.	
VIH	High Level Input Voltage	2.7 to 3.6			2.0		V
VIL	Low Level Input Voltage	2.7 10 3.0				0.8	V
Vон	High Level Output Voltage	2.7 to 3.6		l ₀ =-100 μA	V _{CC} -0.2		
		2.7	VI = VIH	I _O =-12 mA	2.2		V
		3.0	or V _{IL}	I _O =-18 mA	2.4]
		3.0		I _O =-24 mA	2.2		
Vol	Low Level Output Voltage	2.7 to 3.6		I _O =100 μA		0.2	
		2.7	VI = VIH	l _O =12 mA		0.4	v
		3.0	or V _{IL}	l _O =16 mA		0.4	
		3.0		l ₀ =24 mA		0.55	
l _l	Input Leakage Current	2.7 to 3.6	V _I =	0 to 5.5 V		±5	μA
loz	3 State Output Leakage Current	2.7 to 3.6		V _{IH} or V _{IL} ⊧0 to 5.5V		±5	μA
I _{off}	Power Off Leakage Current	0	V_1 or V_0 =	=5.5V (per pin)		10	μA
lcc	Quiescent Supply Current	2.7 to 3.6	VI = V	or GND		20	
			· ·	or V _O = S to 5.5V		±20	μA
Δlcc	ICC incr. per input	2.7 to 3.6	ViH =	V _{CC} -0.6V		500	μA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Parameter Test Conditions		Value			Unit	
		Vcc		Т	₄ = 25 °	°C		
		(V)		Min.	Тур.	Max.		
VOLP	Dynamic Low Voltage Quiet Output	3.3	$C_L = 50 \text{ pF}$		0.8			
Volv	(note 1)		$V_{IL} = 0 V$ $V_{IH} = 3.3V$		-0.8		V	

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.



Symbol	Parameter	Test	Condition	Va	lue	Unit	
		Vcc	Waveform	-40 to	85 °C		
		(V)		Min.	Max.		
t PLH	Propagation Delay Time	2.7	1	1.5	6.5	ns	
t _{PHL}		3.0 to 3.6	1	1.5	6.2	115	
t _{PZL}	Output Enable Time to HIGH and LOW	2.7	2	1.5	6.3	ne	
tрzн	level	3.0 to 3.6	2	1.5	6.1	ns	
t _{PLZ}	Output Disable Time from HIGh and	2.7	2	1.5	6.2	20	
t _{₽HZ}	LOW level	3.0 to 3.6	2	1.5	6.0	ns	
ts	Setup Time, HIGh or LOW level Dn to	2.7	1	2.5			
	CP	3.0 to 3.6		2.5		ns	
t _h	Hold Time, HIGh or LOW level Dn to CP	2.7	1	1.5		ns	
		3.0 to 3.6	I	1.5		115	
tw	CP Pulse Width, HIGH or LOW	2.7	3	3.0		ns	
		3.0 to 3.6	5	3.0		115	
f _{MAX}	Clock Pulse Frequency	3.0 to 3.6	1	170		MHz	
t _{OSLZ} tosн∟	Output to Output Skew Time (note 1, 2)	3.0 to 3.6			1.0	ns	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, $R_L = 500 \Omega$, Input $t_r = t_f = 2.5 \text{ ns}$)

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PLHm} - t_{PLHn}|$)

2) Parameter guaranteed by design

CAPACITIVE CHARACTERISTICS

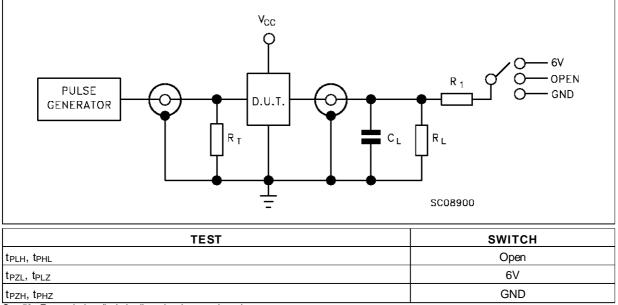
Symbol	Parameter	Test Conditions		Value			Unit
		Vcc	$T_A = 25$		T _A = 25 °		
		(V)		Min.	Тур.	Max.	
CIN	Input Capacitance	3.3	$V_{IN} = 0$ to V_{CC}		7		рF
Сол	Output Capacitance	3.3	$V_{IN} = 0$ to V_{CC}		8		рF
C _{PD}	Power Dissipation Capacitance (note 1)	3.3	$f_{IN} = 10MHz$ $V_{IN} = 0 \text{ or } V_{CC}$		20		pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. Average operting current can be obtained by the following equation. $l_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/n$ (per circuit)



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TEST CIRCUIT

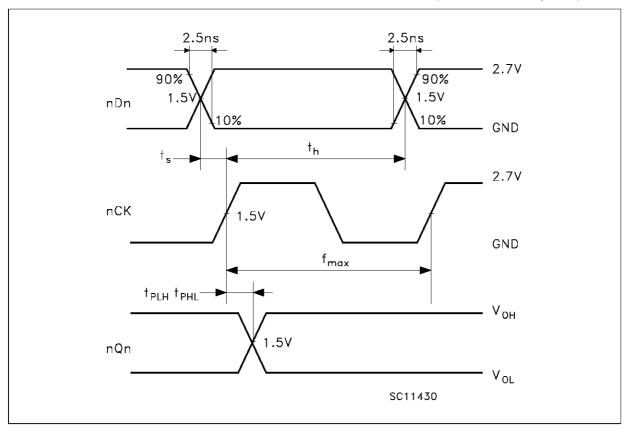


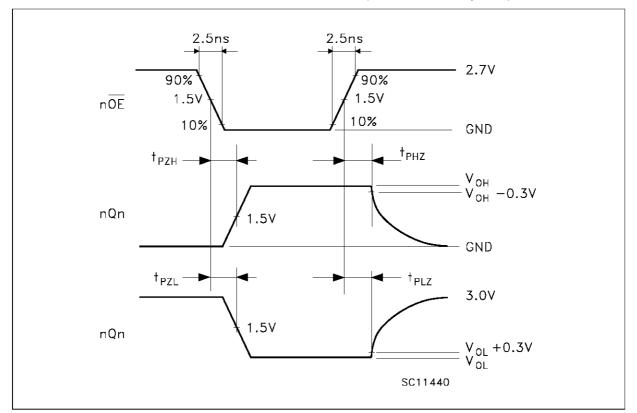
 $C_L = 50 \text{ pF}$ or equivalent (includes jig and probe capacitance)

 $R_L = R_1 = 500 \Omega$ or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

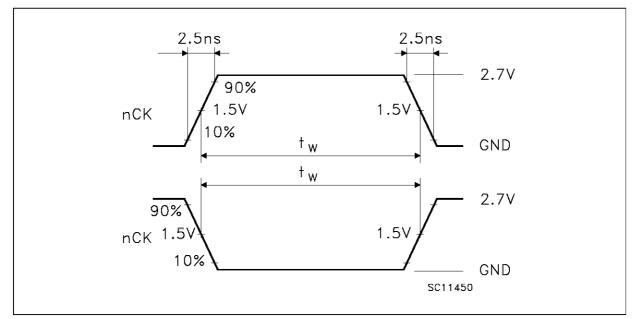
WAVEFORM 1: PROPAGATION DELAYS, SETUP AND HOLD TIMES (f=1MHz; 50% duty cicle)





WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIMES (f=1MHz; 50% duty cicle)

WAVEFORM 3: PULSE WIDTH

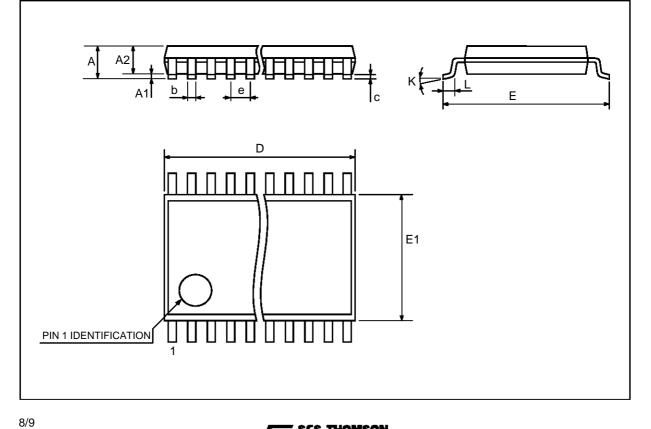




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DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.17		0.27	0.0067		0.011
С	0.09		0.20	0.0035		0.0079
D	12.4	12.5	12.6	0.408	0.492	0.496
Е	7.95	8.1	8.25	0.313	0.319	0.325
E1	6.0	6.1	6.2	0.236	0.240	0.244
е		0.5 BSC			0.0197 BSC	
К	0°	4 ^o	8°	0°	4 ⁰	8°
L	0.50	0.60	0.70	0.020	0.024	0.028





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